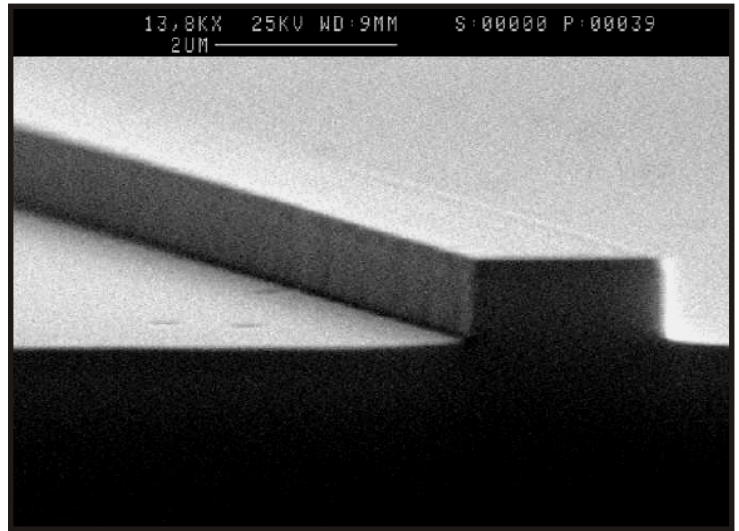
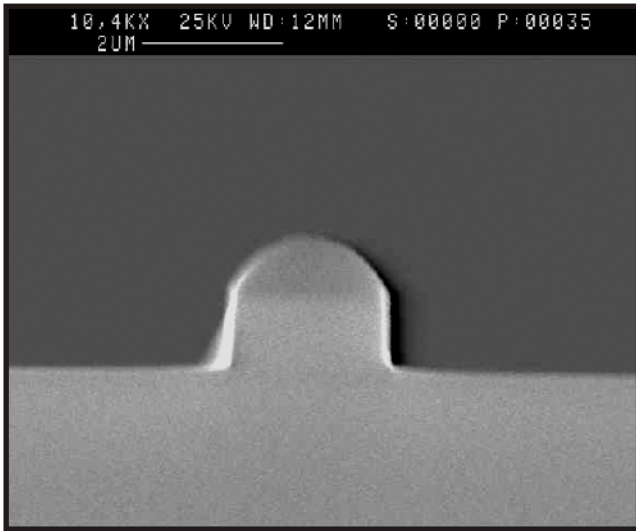


# Plasmalab Data

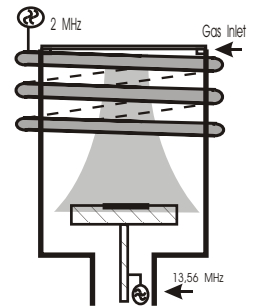
## GaAs/GaInP/AlInGaP Waveguide Etch



OPT application lab:  
Vertical etched profile (with PR mask)

OPT application lab:  
PR mask was taken off by Acetone

- Plasmalab System 100*
- Plasmalab System 133*
- Plasmalab 80 Plus*



3  $\mu\text{m}$  deep anisotropic etch with  
- no "trenching", - no "foot"



**Technology:**  
ICP - RIE  
Cl based process  
PR mask hard baked

**Results:**  
Etch rate > 0.25  $\mu\text{m}/\text{min}$  (total)  
Uniformity <  $\pm 4\%$  on 2" wafer  
Selectivity > 8:1 to PR mask (total)  
Profile control: vertical > 80°